

4V Drive Pch MOSFET

RQ1E070RP

Structure

Silicon P-channel MOSFET

● Features

- 1) Low On-resistance.
- 2) High power package.
- 3) 4V drive.

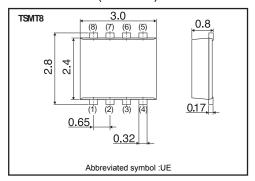
Application

Switching

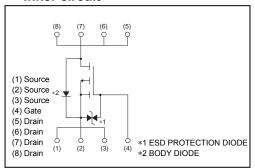
Packaging specifications

	Package	Taping
Type	Code	TR
	Basic ordering unit (pieces)	3000
RQ1E070RP		0

• Dimensions (Unit : mm)



• Inner circuit



● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	-30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I _D	±7	Α
	Pulsed	I _{DP} *1	±28	Α
Source current	Continuous	Is	-1	Α
(Body Diode)	Pulsed	I _{SP} *1	-28	Α
Power dissipation		P _D *2	1.5	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

^{*1} Pw \leq 10 μ s, Duty cycle \leq 1%

• Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	83.3	°C / W

^{*}Mounted on a ceramic board.

^{*2} Mounted on a ceramic board.

● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μ A	$V_{GS}=\pm20V$, $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	I_D =-1mA, V_{GS} =0V
Zero gate voltage drain current	I _{DSS}	ı	1	-1	μA	V_{DS} =-30V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	-1.0	-	-2.5	V	V_{DS} =-10V, I_{D} =-1mA
Static drain acures on state	*	ı	12	17		I _D =-7A, V _{GS} =-10V
Static drain-source on-state resistance	R _{DS (on)}	-	17	24	mΩ	$I_D = -3.5A, V_{GS} = -4.5V$
		ı	19	27		$I_D = -3.5A, V_{GS} = -4.0V$
Forward transfer admittance	IY _{fs} ľ	6	1	-	S	I _D =-7A, V _{DS} =-10V
Input capacitance	C _{iss}	ı	2700	-	pF	V _{DS} =-10V
Output capacitance	C _{oss}	ı	390	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	ı	350	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	1	16	-	ns	I _D =-3.5A, V _{DD} ≒-15V
Rise time	t _r *	ı	35	-	ns	V _{GS} =-10V
Turn-off delay time	t _{d(off)} *	ı	140	-	ns	R _L ≒4.3Ω
Fall time	t _f *	ı	70	-	ns	R_G =10 Ω
Total gate charge	Q _g *	-	26	-	nC	I _D =-7A, V _{DD} ≒-15V
Gate-source charge	Q _{gs} *	-	7.5	-	nC	V _{GS} =–5V R _L ≒ 2.1Ω
Gate-drain charge	Q _{gd} *	-	8.0	-	nC	R_G =10 Ω

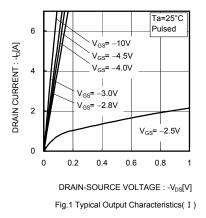
^{*}Pulsed

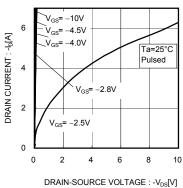
●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^{*}	-	-	-1.2	V	$I_s=-7A$, $V_{GS}=0V$

^{*}Pulsed

Electrical characteristic curves





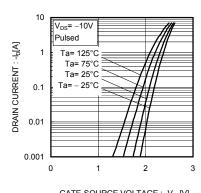


Fig.2 Typical Output Characteristics(II)

 $\label{eq:GATE-SOURCE VOLTAGE:-VGS} GATE-SOURCE \ VOLTAGE:-V_{GS}[V]$ Fig.3 Typical Transfer Characteristics

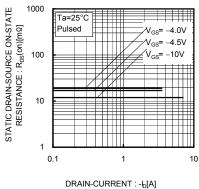


Fig.4 Static Drain-Source On-State
Resistance vs. Drain Current(I)

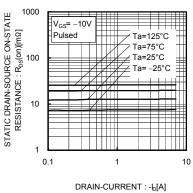


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

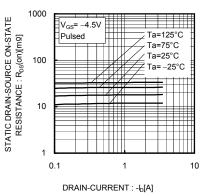


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(皿)

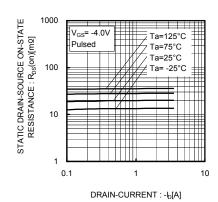


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

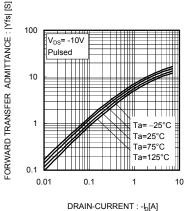


Fig.8 Forward Transfer Admittance vs. Drain Current

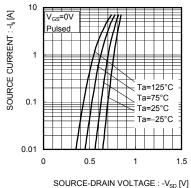
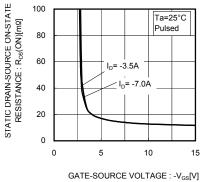
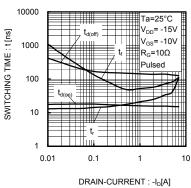


Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage







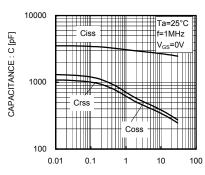
GATE-SOURCE VOLTAGE: -V_{GS} [V] 4 Ta=25°C V_{DD}= -15V $I_D = -7A$ $R_G = 10\Omega$ Pulsed 20 40 50 0 10 30 TOTAL GATE CHARGE : Qg [nC]

10

Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

Fig.11 Switching Characteristics

Fig.12 Dynamic Input Characteristics



DRAIN-SOURCE VOLTAGE : $-V_{DS}[V]$ Fig.13 Typical Capacitance vs. Drain-Source Voltage

Measurement circuits

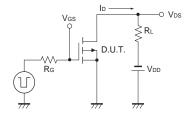


Fig.1-1 Switching time measurement circuit

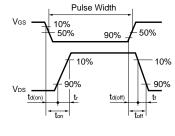


Fig.1-2 Switching Waveforms

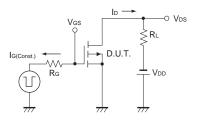


Fig.2-1 Gate charge measurement circuit

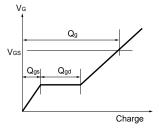


Fig.2-2 Gate Charge Waveform

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